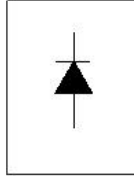


International  
**IOR** Rectifier

**SAFEIR** Series  
 60EPS..

INPUT RECTIFIER DIODE



$V_F < 1V @ 30A$   
 $I_{FSM} = 950A$   
 $V_{RRM} 800 \text{ to } 1600V$

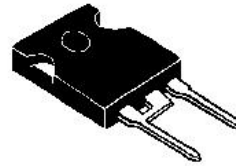
Description/Features

The 60EPS.. rectifier SAFEIR series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150° C junction temperature. Typical applications are in input rectification and these products are designed to be used with International Rectifier Switches and Output Rectifiers which are available in identical package outlines.

Major Ratings and Characteristics

Characteristics	60EPS..	Units
$I_F$ (AV) Sinusoidal waveform	60	A
$V_{RRM}$	800 to 1600	V
$I_{FSM}$	950	A
$V_F @ 30A, T_J = 25^\circ C$	1.0	V
$T_J$	-40 to 150	°C

Package Outline



TO-247AC (Modified)

Voltage Ratings

Part Number	$V_{RRM}$ maximum peak reverse voltage VV	$V_{RSM}$ maximum non repetitive peak reverse voltage	$I_{FRM}$ 150°C mA
60EPS08	800	900	1
60EPS12	1200	1300	
60EPS16	1600	1700	

Absolute Maximum Ratings

Parameters	60EPS..	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current	60	A	@ $T_J=118^{\circ}\text{C}, 180^{\circ}\text{C}$ conduction half sine wave
$I_{FSM}$ Max. Peak One Cycle Non-Repetitive Surge Current	950	A	10ms Sine pulse, rated $V_{RRM}$ applied
	1100		10ms Sine pulse, no voltage reappplied
$I_{2t}$ Max. $I^2t$ for fusing	4512	A <sup>2</sup> s	10ms Sine pulse, rated $V_{RRM}$ applied
	6300		10ms Sine pulse, no voltage reappplied
$I_{2\sqrt{t}}$ Max. $I^2\sqrt{t}$ for fusing	63000	A <sup>2</sup> $\sqrt{s}$	$t = 0.1$ to 10ms, no voltage reappplied

Electrical Specifications

Parameters	60EPS..	Units	Conditions
$V_{FM}$ Max. Forward Voltage Drop	1.07	V	@ 60A, $T_J=25^{\circ}\text{C}$
$r_f$ Forward slope resistance	3.96	m $\Omega$	$T_J=150^{\circ}\text{C}$
$V_{F(TO)}$ Threshold voltage	0.74	V	
$I_{RM}$ Max. Reverse Leakage Current	0.1	mA	$T_J=25^{\circ}\text{C}$
	1.0		$T_J=150^{\circ}\text{C}$

$V_R = \text{rated } V_{RRM}$

Thermal-Mechanical Specifications

Parameters	60EPS..	Units	Conditions
$T_J$ Max. Junction Temperature Range	-40 to 150	$^{\circ}\text{C}$	
$T_{stg}$ Max. Storage Temperature Range	-40 to 150	$^{\circ}\text{C}$	
$R_{thJC}$ Max. Thermal Resistance Junction to Case	0.35	$^{\circ}\text{C}/\text{W}$	DC operation
$R_{thJA}$ Max. Thermal Resistance Junction to Ambient	40	$^{\circ}\text{C}/\text{W}$	
$R_{thCS}$ Typical Thermal Resistance, Case to Heatsink	0.2	$^{\circ}\text{C}/\text{W}$	Mounting surface, smooth and greased
wt Approximate Weight	6(0.21)	g(oz.)	
T Mounting Torque	Min. 6(5)	Kg-cm (lbf-in)	
	Max. 12(10)		
Case Style	TO-247AC		JEDEC(Modified)

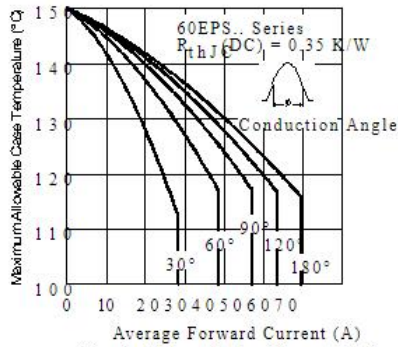


Fig. 1 - Current Rating Characteristics

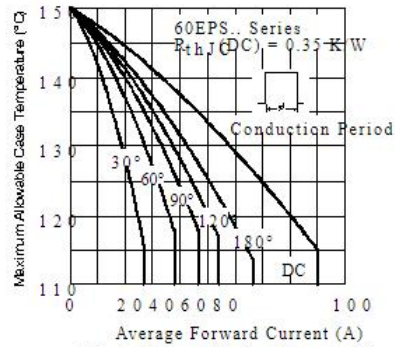


Fig. 2 - Current Rating Characteristics

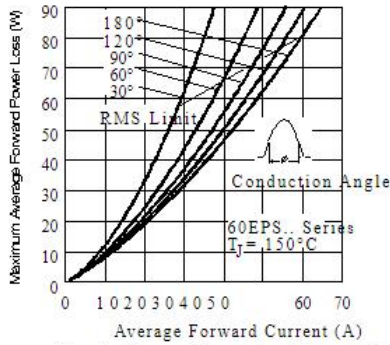


Fig. 3 - Forward Power Loss Characteristics

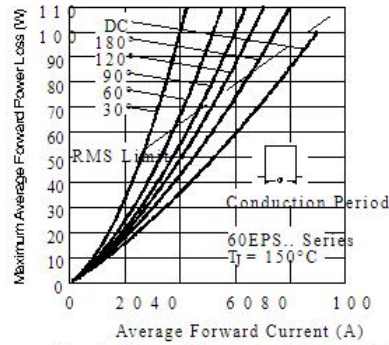


Fig. 4 - Forward Power Loss Characteristics

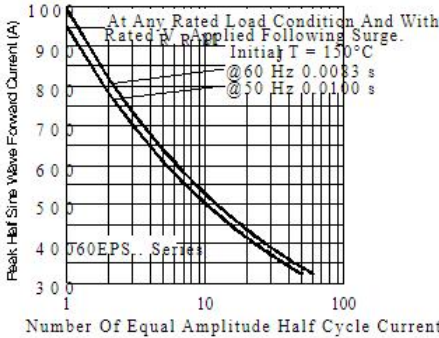


Fig. 5 - Maximum Non-Repetitive Surge Current

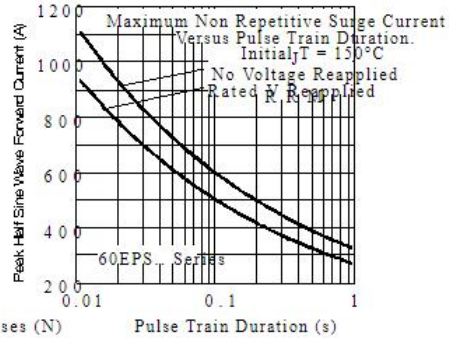


Fig. 6 - Maximum Non-Repetitive Surge Current

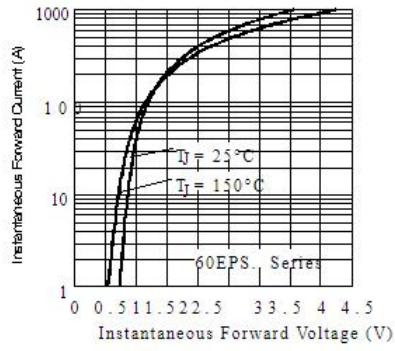


Fig. 7 - Forward Voltage Drop Characteristics

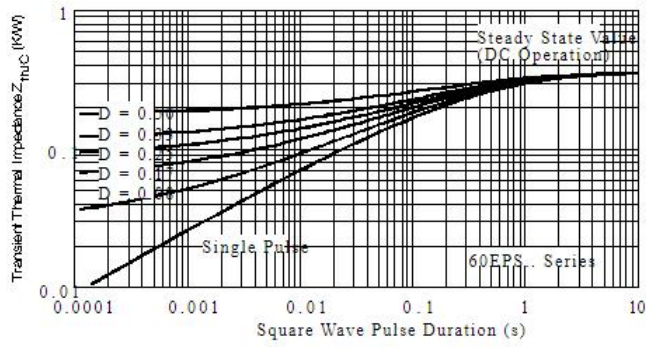
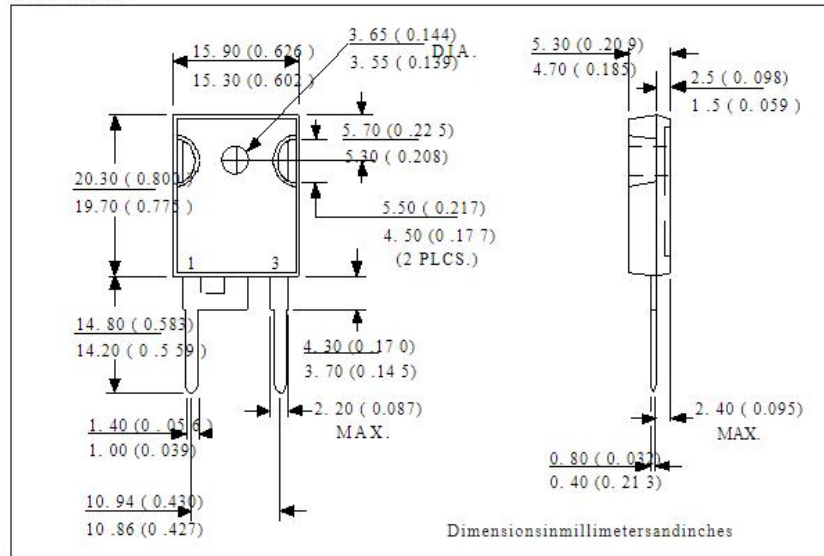


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

Outline Table



Ordering Information Table

Device Code				
<b>60</b>	<b>E</b>	<b>P</b>	<b>S</b>	<b>16</b>
①	②	③	④	⑤
<b>1</b>	- Current Rating			
<b>2</b>	- Circuit Configuration: E = Single Diode			
<b>3</b>	- Package: P = TO-247AC (Modified)			
<b>4</b>	- Type of Silicon: S = Standard Recovery Rectifier			
<b>5</b>	- Voltage code: Code x 100 $\frac{V}{RRM}$			
			08 = 800V	
			12 = 1200V	
			16 = 1600V	

BASE CATHODE  
 ②  
 ① ③  
 CATHODE ANODE